

Title (en)

METHOD OF FABRICATING A MICROELECTRONIC STRUCTURE INVOLVING MOLECULAR BONDING

Title (de)

VERFAHREN ZUR HERSTELLUNG EINER MIKROELEKTRONISCHEN STRUKTUR UNTER BETEILIGUNG VON MOLEKULARBINDUNG

Title (fr)

PROCÉDÉ DE FABRICATION D'UNE STRUCTURE MICRO-ÉLECTRONIQUE IMPLIQUANT UN COLLAGE MOLÉCULAIRE

Publication

EP 2195835 A1 20100616 (FR)

Application

EP 08869784 A 20081010

Priority

- FR 2008001427 W 20081010
- FR 0758282 A 20071012

Abstract (en)

[origin: FR2922359A1] The method involves preparing a donor substrate (1) with a semiconductor material surface, where the material is chosen from one of silicon, germanium, gallium nitride, gallium arsenide, lithium tantalate and lithium niobate. A coating layer (3), made of a material such as oxides, metallic element, metallic alloy, silicon oxynitride and nitride, is formed at the semiconductor material surface by an ion-beam sputtering, where the layer has a free surface. A molecule of the free surface is mounted on a face of a receptor substrate (4).

IPC 8 full level

H01L 21/762 (2006.01)

CPC (source: EP US)

H01L 21/0214 (2013.01 - EP US); **H01L 21/02164** (2013.01 - US); **H01L 21/0217** (2013.01 - EP US); **H01L 21/02181** (2013.01 - EP US); **H01L 21/02183** (2013.01 - EP US); **H01L 21/02186** (2013.01 - EP US); **H01L 21/02266** (2013.01 - US); **H01L 21/2007** (2013.01 - EP US); **H01L 21/76254** (2013.01 - EP US); **H01L 21/02164** (2013.01 - EP); **H01L 21/02266** (2013.01 - EP); **H01L 21/31604** (2013.01 - US); **H01L 21/318** (2013.01 - US)

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